| Name: Enrolment No: | | VPES | | |
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| LIIIOI | ment no. | UNIVERSITY OF TOMORROW | | |
| | | UPES | | |
| | Ene | d Semester Examination, Dec 2024 | | |
| Programme Name: MSc Physics Semester: I | | | | |
| Course Name: Analog Electronics Time: 03 hrs | | | | |
| | e Code: ECEG7034 | Max. Marks: 100 | | |
| | f page(s):2 | | | |
| Instru | ctions: [a] A scientific calculator is | s allowed. [b] Symbols have their usual meanings | | |
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| | | SECTION A Answer all questions | | |
| S.No. | | | Marks | CO |
| Q 1 | Derive the expression for the intrin | nsic carrier concentration (n _i) in a semiconductor. | 5 | CO1 |
| Q 2 | For a reverse-biased P-N junction, derive the expression for junction capacitance (Cj) and explain how it varies with the applied reverse voltage. | | 5 | CO2 |
| Q 3 | A silicon P-N junction diode has a reverse saturation current of $I_s = 10^{-12}A$ at 300K. Calculate the forward current when the diode is forward-biased with a voltage of 0.7 V. (Use kT/q=0.0259V). | | 5 | CO3 |
| Q 4 | What is Op-Amp. Briefly describe the five practical applications of Op-Amps in the electronics industry. | | 5 | CO4 |
| | | SECTION B | | |
| | Answer a | all questions (Q 5 has an internal choice) | | |
| Q 5 | In a silicon sample at 300 K, the e | lectron mobility μ_n is 1350 cm ² /V-s, and the hole mobility | | |
| Q J | μ_p is 480 cm ² /V-s. An electric field drift current density J _{drift} if the elec p=10 ¹⁵ cm ^{-3.} | E of 1000 V/cm is applied across the sample. Calculate the ctron concentration $n=10^{16}$ cm ⁻³ and the hole concentration OR tionship between diffusion coefficient and mobility) for a | 10 | CO1 |
| Q 6 | Sketch the I-V characteristics of application of LEDs in optoelectro | an LED. Explain how LEDs emit light, and describe one onics. | 10 | CO2 |
| Q7 | | emitter resistor R_E in a common-emitter amplifier circuit. ribute to the stability of the amplifier's operating point? | 10 | CO3 |
| Q8 | | feedback capacitor, $C=1\mu F$ and an input resistor, $R=100k\Omega$. is applied, find the output voltage V_{out} as a function of time. | 10 | CO4 |
| | | | 1 | 1 |

| SECTION C Answer any one question (Question 10 has an internal choice) | | | | | |
|---|---|--------------------------------|-----|--|--|
| Q 9 | What is FET? What are the differences between FET and BJT? Give the construction and working of n channel JFET with a proper diagram. Explain the output characteristics and transfer characteristics of n-channel JFET. | 2+5+7 +6 | CO3 | | |
| Q 10 | [a] What is feedback? Explain the negative feedback with a diagram. Derive the expression of its voltage gain. [b]An inverting amplifier circuit is built with an operational amplifier, where the input resistor R_{in}= 5kΩ and the feedback resistor R_f= 50 kΩ. If the input voltage V_{in}= 0.5V, calculate the output voltage V_{out}. Assume an ideal op-amp. OR [a] Explain how an Op-Amp works as an integrator. Provide an example of a real-world | tor the 10+10 CO4 | | | |
| | [a] Explain now an Op-Amp works as an integrator. Provide an example of a real-world application [b] Derive the Barkhausen criterion for oscillation and explain why it is necessary for oscillator circuits | | | | |